

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE

2SD2092

SWITCHING APPLICATIONS

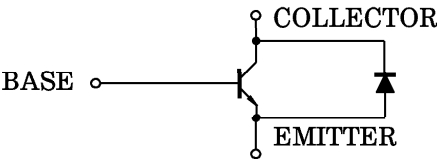
LAMP, SOLENOID DRIVE APPLICATIONS

- High DC Current Gain : $h_{FE(1)}=500\sim1500$
- Low Collector Saturation Voltage
: $V_{CE(sat)}=0.3V$ (Max.)

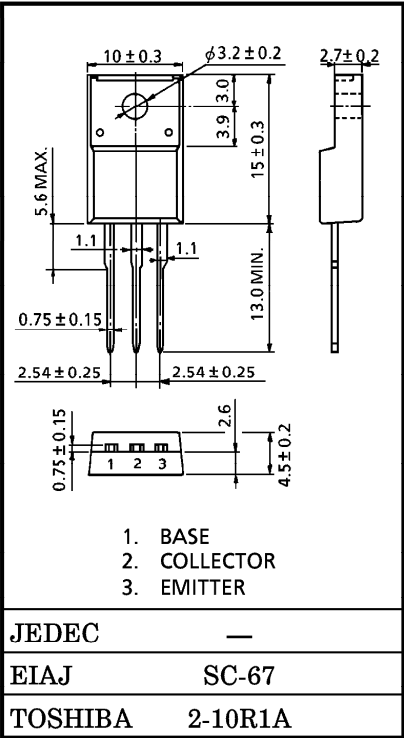
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		VCBO	100	V
Collector-Emitter Voltage		VCEO	100	V
Emitter-Base Voltage		VEBO	7	V
Collector Current	DC	IC	3	A
	Pulse	ICP	5	
Base Current		IB	1	A
Collector Power Dissipation	Ta = 25°C	PC	2.0	W
	Tc = 25°C		25	
Junction Temperature		Tj	150	°C
Storage Temperature Range		Tstg	-55~150	°C

EQUIVALENT CIRCUIT



Unit in mm

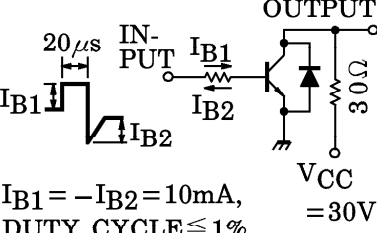


Weight : 1.7g (Typ.)

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} = 100V, I _E = 0	—	—	10	μA
Emitter Cut-off Current		IEBO	V _{EB} = 7V, I _C = 0	—	—	10	μA
Collector-Emitter Breakdown Voltage		V _(BR) CEO	I _C = 50mA, I _B = 0	100	—	—	V
DC Current Gain		h _{FE} (1)	V _{CE} = 1V, I _C = 0.5A	500	—	1500	
		h _{FE} (2)	V _{CE} = 1V, I _C = 1A	150	—	—	
Collector-Emitter Saturation Voltage		V _{CE} (sat)	I _C = 1A, I _B = 10mA	—	—	0.3	V
Base-Emitter Saturation Voltage		V _{BE} (sat)	I _C = 1A, I _B = 10mA	—	—	1.2	V
Collector-Emitter Forward Voltage		V _{ECF}	I _E = 1A, I _B = 0	—	—	2.0	V
Transition Frequency		f _T	V _{CE} = 5V, I _C = 0.5A	—	140	—	MHz
Collector Output Capacitance		C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	30	—	pF
Switching Time	Turn-on Time	t _{on}	 I _{B1} = -I _{B2} = 10mA, DUTY CYCLE ≤ 1%	—	0.5	—	μs
	Storage Time	t _{stg}		—	5	—	
	Fall Time	t _f		—	0.7	—	

